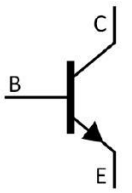
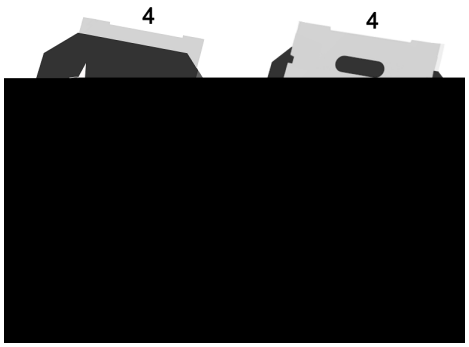
TO-252 NPN Silicon NPN transistor in a TO-252 Plastic Package.

AEC-Q101

High collector-Emitter breakdown voltage, Suitable for transformer, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

High voltage general purpose applications, Meet the stringent requirements of automotive applications.



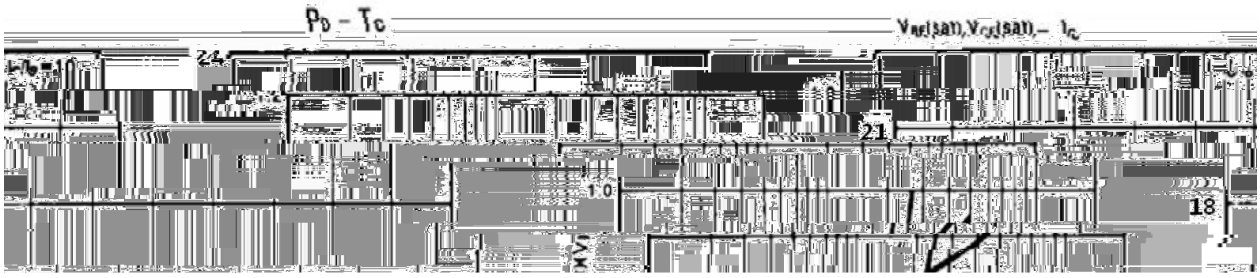


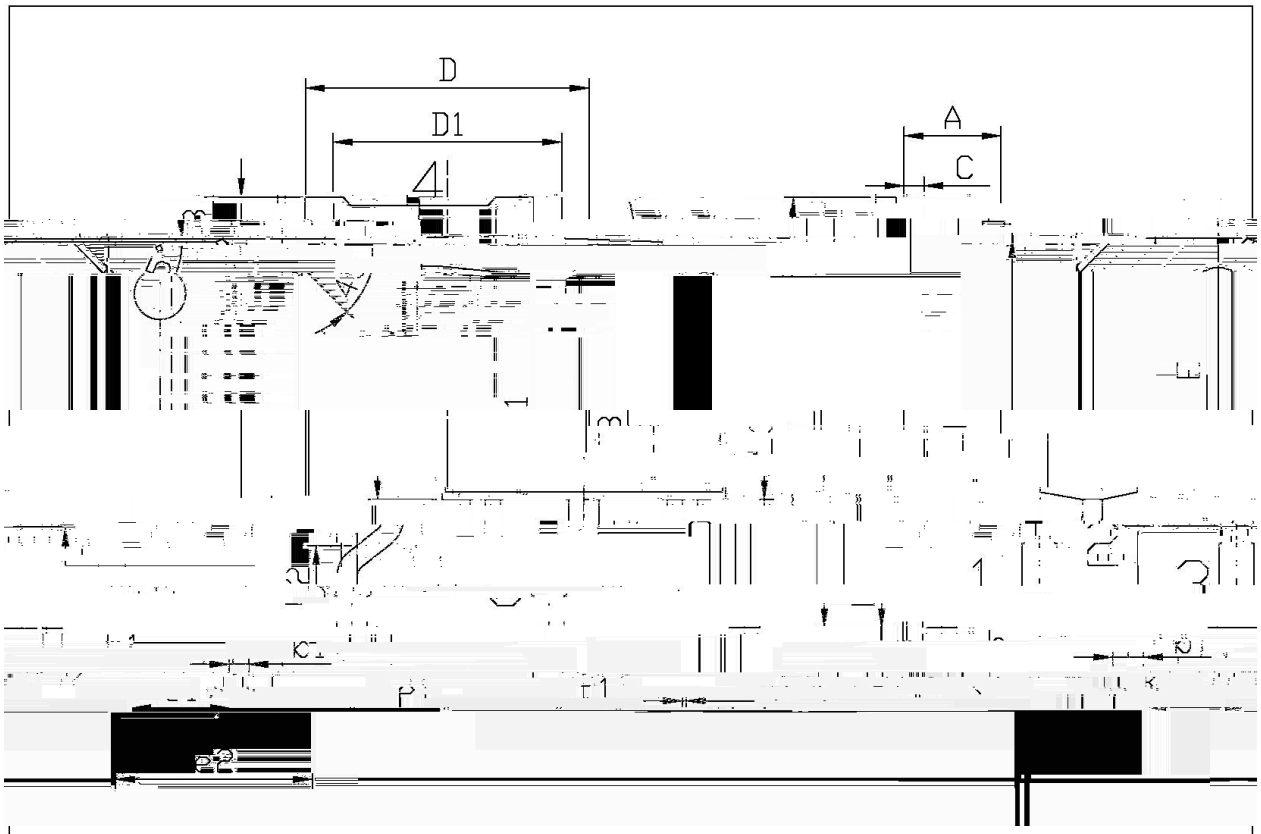
PIN1 Base PIN 2,4 Collector PIN 3 Emitter

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	300	V
Collector to Emitter Voltage	V_{CEO}	300	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	500	mA
Collector Power Dissipation	P_C	1.56	W
Collector Power Dissipation	$P_C(T_C=25$)	15	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ

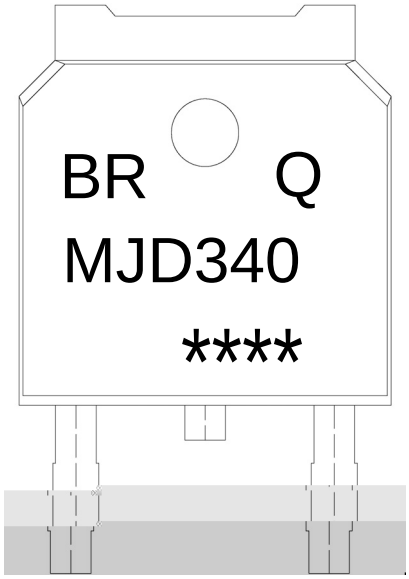

P_D – T_C
V_BE(sat), V_CE(sat) – I_C
24
21
18
10



单位：mm

Dimensions In Millimeters			Dimensions In Millimeters		
	Min.	Max.		Min.	Max.
E	6.35	6.75	A	2.20	
B	0.95	1.25			
b	0.70				
C	0.45	0.55	L2	1.70	2.00
D1	5.10	5.50	K	0.00	

TO-252



BR

Q

MJD340

****

Note:

BR:	Company Code
Q:	Automobile halogen-free product Code
MJD340:	Product Type
****:	Lot No. Code, code change with Lot No